

EAST: (10644902 buried source line.wsp:1)

FileViewEditToolsWindowHelp

Pending

Active

L12: (16352) sheet adj resistance

L13: (10262) source near resistance

L14: (25547) L12 L13

L15: (476) etox

L16: (31) L15 and L14

L17: (557393) FOX field adj oxide STI (isolat\$3 element adj (insulat\$4 separat\$4)

L18: (1177740) (perpendicular \$2 orthogonal\$3)

L19: (1783) L17 near\$ L18

L20: (20) L15 and L19

L21: (48) 16 20

L22: (2687685) source

L23: (47) 21 and 17

L24: (47) 23 and 22

L25: (9) Backward citation search 3

L26: (3) Forward citation search 4

L27: (57528) source near (line common)

L28: (1863886) buried substrate

L29: (481) 27 near 28

L30: (841) 27 near\$ 17

L31: (354) 28 same 30

L32: (41) 29 same 30

L33: (41) 32 and 27

L34: (41) 33 and 17

Failed

DBsUS:PCPLB:USPAT:EPO:JPO:DERVENT:ISM:TDB

Default operator:OR

29 same 30

Jan. 2005

Phrases

Highlight all hit terms initially

BAS formISAR formImageTextHTML

	U	Inventor	Document#	Issue	P	Title	Current	CurrentXR	Retrieval	S	C	P	S	S	S	Image	Doc	P
1	<input checked="" type="checkbox"/>	R	Song, Yun-He	US 6835532	20031	1	Method for fabricating NOR type flash memo	438/259	257/E21.68		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 683553	<input checked="" type="checkbox"/>
2	<input checked="" type="checkbox"/>	F	Lee, Robin et	US 6211012	20010	1	Method of fabricating an ETOX flash memory	438/257	257/E21.68		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 621101	<input checked="" type="checkbox"/>
3	<input checked="" type="checkbox"/>	F	Lee, Robin	US 6372584	20020	9	Method of manufacturing Vshaped flash me	438/192	257/E29.30		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 637258	<input checked="" type="checkbox"/>
4	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004022	20041	3	Fabrication of dielectric on a gate surface to	438/585	438/197		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200402	<input checked="" type="checkbox"/>
5	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004022	20041	3	FABRICATION OF GATE DIELECTRIC IN NON	438/257			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200402	<input checked="" type="checkbox"/>
6	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004022	20041	3	FABRICATION OF GATE DIELECTRIC IN NON	257/315			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200402	<input checked="" type="checkbox"/>
7	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004020	20041	5	NONVOLATILE MEMORIES WITH A FLOATIN	257/315	257/316		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200402	<input checked="" type="checkbox"/>
8	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004018	20040	4	Nonvolatile memories and methods of fabrica	438/257	438/258		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200401	<input checked="" type="checkbox"/>
9	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004018	20040	5	Nonvolatile memories and methods of fabrica	438/257	257/316		<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200401	<input checked="" type="checkbox"/>
10	<input checked="" type="checkbox"/>	F	Ding, Yi	US 2004018	20040	4	Fabrication of integrated circuit elements in	438/257			<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	<input checked="" type="checkbox"/>	US 200401	<input checked="" type="checkbox"/>

FileDetailsHTML

Ready

NUM